

FDA69N25

N-Channel UniFET™ MOSFET

250 V, 69 A, 41 mΩ

Features

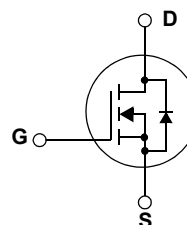
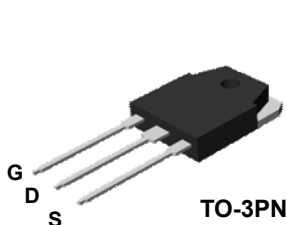
- $R_{DS(on)} = 41 \text{ m}\Omega$ (Max.) @ $V_{GS} = 10 \text{ V}$, $I_D = 34.5 \text{ A}$
- Low Gate Charge (Typ. 77 nC)
- Low Crss (Typ. 84 pF)

Applications

- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

Description

UniFET™ MOSFET is Fairchild Semiconductor®'s high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as PFC, FPD TV power, ATX and lighting ballasts.



Absolute Maximum Ratings

Symbol	Parameter		FDA69N25	Unit
V_{DSS}	Drain-Source Voltage		250	V
$V_{DS(Avalanche)}$	Repetitive Avalanche Voltage (Note 1) (Note 2)		300	V
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	69	A
		- Continuous ($T_C = 100^\circ\text{C}$)	44.2	A
I_{DM}	Drain Current	- Pulsed (Note 1)	276	A
V_{GSS}	Gate-Source Voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		1894	mJ
I_{AR}	Avalanche Current (Note 1)		69	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		48	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	480	W
		- Derate above 25°C	3.84	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FDA69N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.26	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDA69N25	FDA69N25	TO-3PN	--	--	30

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA	250	--	--	V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	--	0.25	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 250 V, V _{GS} = 0 V	--	--	1	μA
		V _{DS} = 200 V, T _C = 125°C	--	--	10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0	--	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 34.5 A	--	0.034	0.041	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 34.5 A	--	25	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz	--	3570	4640	pF
C _{oss}	Output Capacitance		--	750	980	pF
C _{rss}	Reverse Transfer Capacitance		--	84	130	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 125 V, I _D = 69A, R _G = 25 Ω	--	95	200	ns
t _r	Turn-On Rise Time		--	855	1720	ns
t _{d(off)}	Turn-Off Delay Time		--	130	270	ns
t _f	Turn-Off Fall Time		(Note 4)	--	220	450
Q _g	Total Gate Charge	V _{DS} = 200 V, I _D = 69A, V _{GS} = 10 V	--	77	100	nC
Q _{gs}	Gate-Source Charge		--	24	--	nC
Q _{gd}	Gate-Drain Charge		(Note 4)	--	37	--
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	34	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	136	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 69 A	--	--	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 69 A, di _F / dt = 100 A/μs	--	210	--	ns
Q _{rr}	Reverse Recovery Charge		--	5.7	--	μC

NOTES:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 0.64mH, I_{AS} = 69A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 69A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Essentially independent of operating temperature

Typical Performance Characteristics

Figure 1. On-Region Characteristics

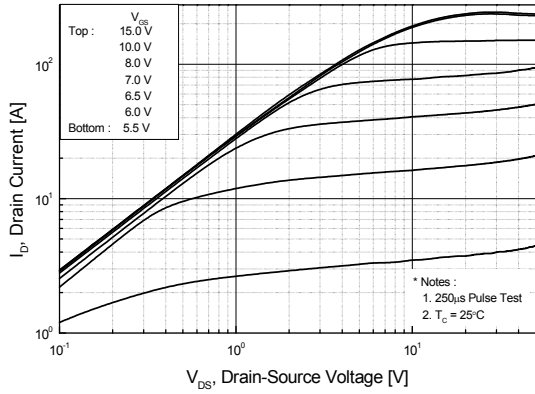


Figure 2. Transfer Characteristics

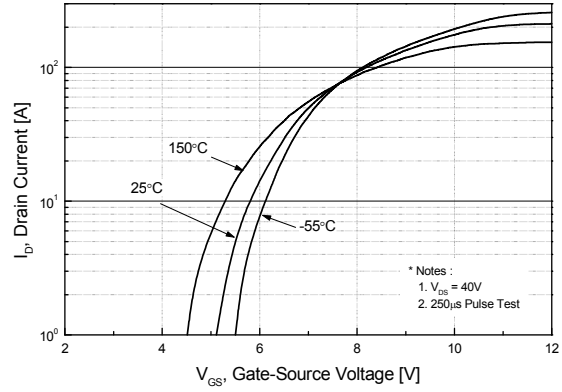


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

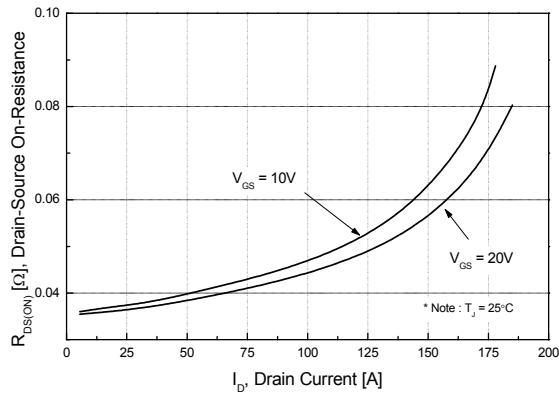


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

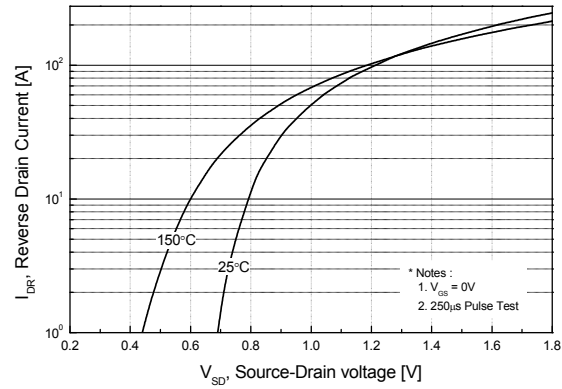


Figure 5. Capacitance Characteristics

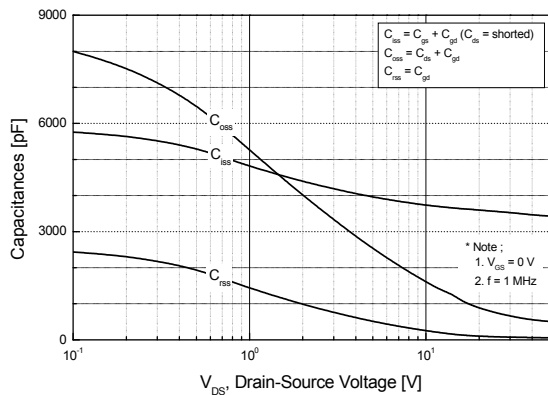
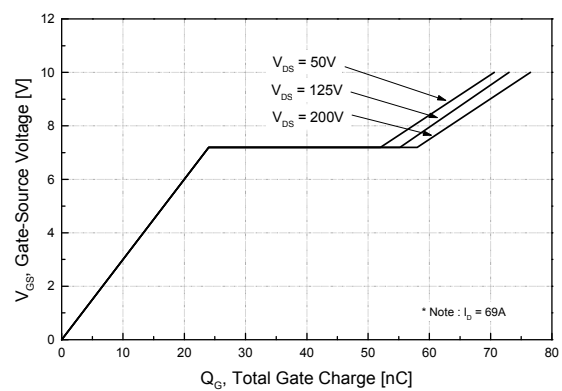


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

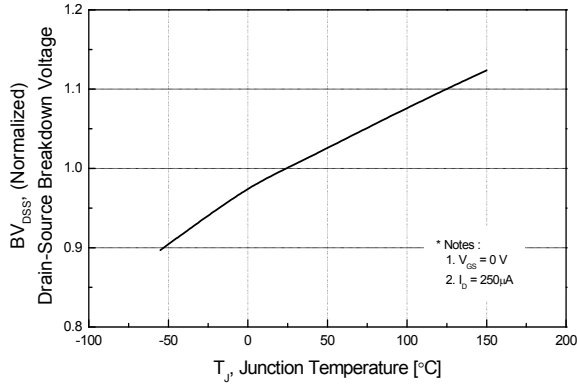


Figure 8. On-Resistance Variation vs. Temperature

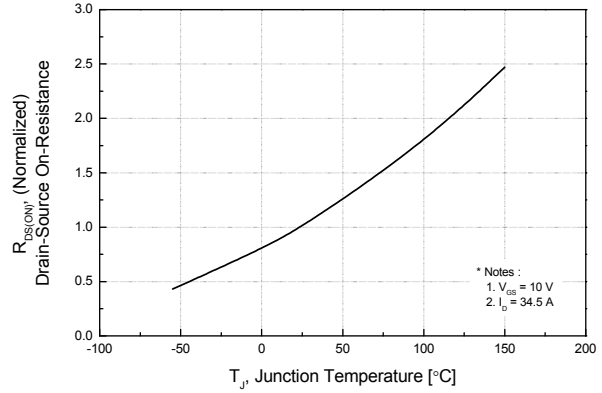


Figure 9. Maximum Safe Operating Area

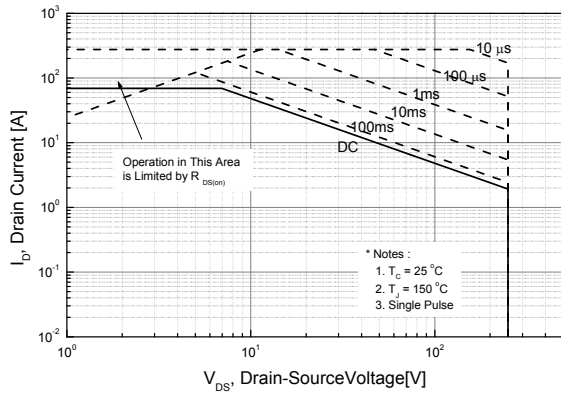


Figure 10. Maximum Drain Current vs. Case Temperature

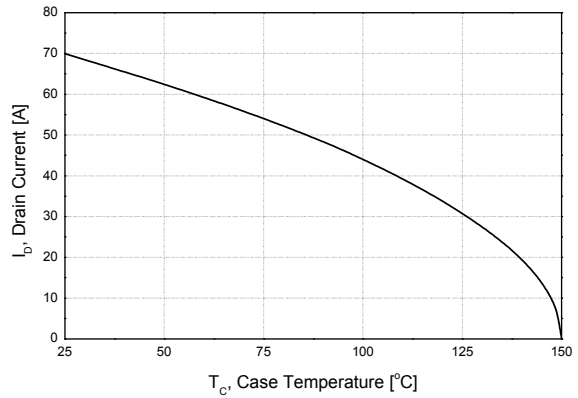
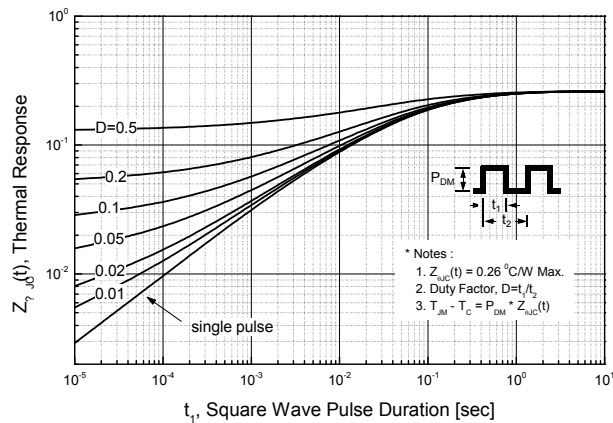
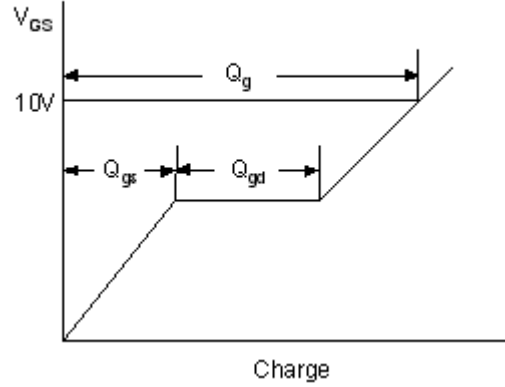


Figure 11. Transient Thermal Response Curve



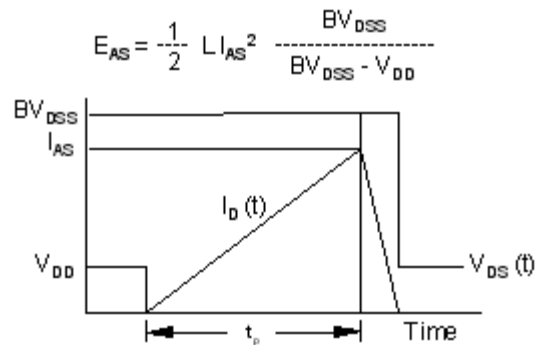
Gate Charge Test Circuit & Waveform



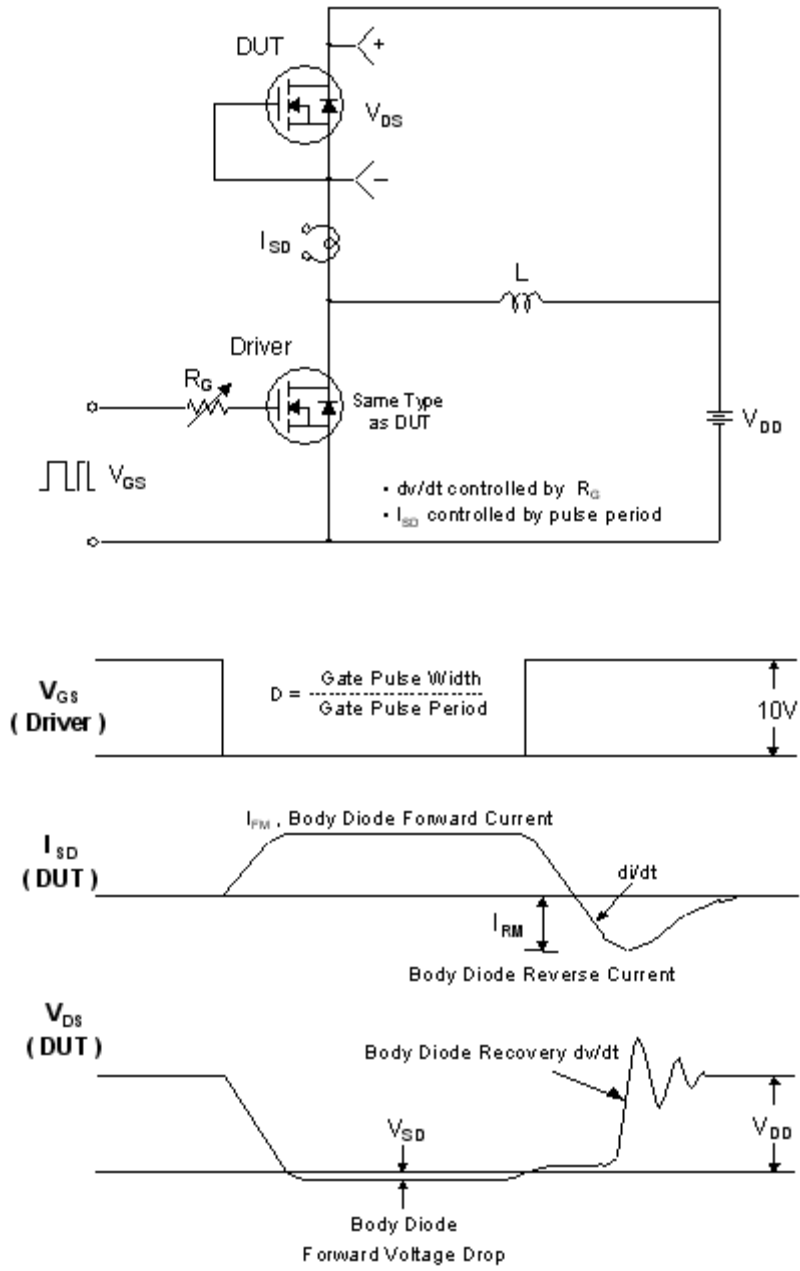
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

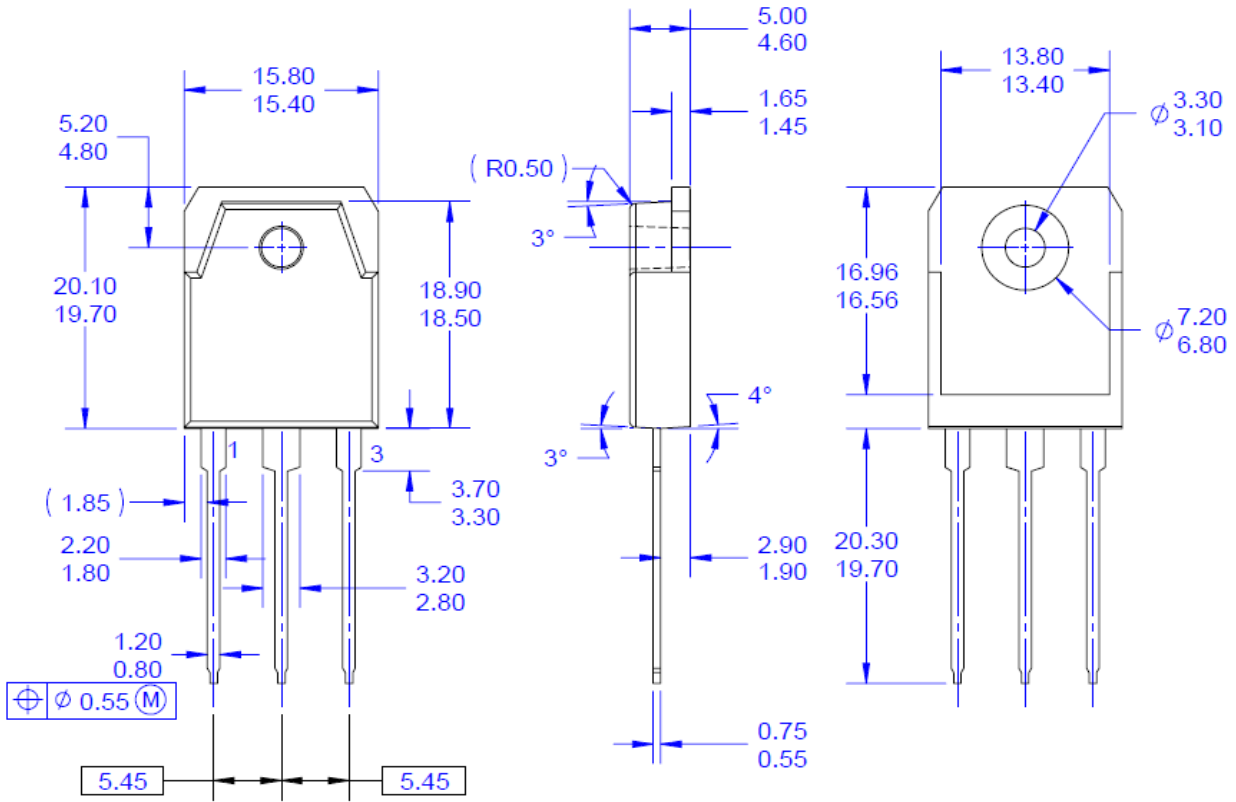


Peak Diode Recovery dv/dt Test Circuit & Waveforms



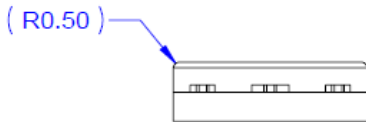
Mechanical Dimensions

TO-3PN



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